

SANYO Semiconductors DATA SHEET

P-Channel Silicon MOSFET

SCH2315 — General-Purpose Switching Device **Applications**

Features

- · Low ON-resistance.
- · Ultrahigh-speed switching.
- 1.8V drive.
- · Composite type with two MOSFETs contained in a single package, facilitating high-density mounting.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		-12	V
Gate-to-Source Voltage	VGSS		±8	V
Drain Current (DC)	ID		-0.9	Α
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	-3.6	Α
Allowable Power Dissipation	PD	Mounted on a ceramic board (900mm ² X0.8mm) 1unit	0.65	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Offic
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=-1mA, VGS=0	-12			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =-12V, V _{GS} =0			-10	μΑ
Gate-to-Source Leakage Current	IGSS	V _{GS} =±6.4V, V _{DS} =0			±10	μΑ
Cutoff Voltage	VGS(off)	VDS=-6V, ID=-100μA	-0.3		-1.0	V
Forward Transfer Admittance	yfs	V _{DS} =-6V, I _D =-500mA	0.6	1		S
Static Drain-to-Source On-State Resistance	R _{DS} (on)1	I _D =-500mA, V _G S=-4.5V		470	615	mΩ
	RDS(on)2	ID=-300mA, VGS=-2.5V		690	970	mΩ
	R _{DS} (on)3	I _D =-100mA, V _G S=-1.8V		920	1380	mΩ
Input Capacitance	Ciss	VDS=-6V, f=1MHz		92		pF
Output Capacitance	Coss	V _{DS} =-6V, f=1MHz		26.5		pF
Reverse Transfer Capacitance	Crss	V _{DS} =-6V, f=1MHz		18		pF

Marking: MQ Continued on next page.

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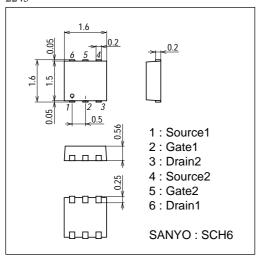
SCH2315

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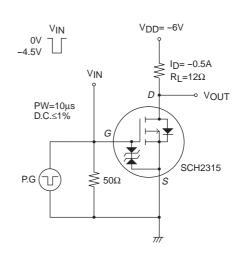
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	O III
Turn-ON Delay Time	t _d (on)	See specified Test Circuit.		8.2		ns
Rise Time	t _r	See specified Test Circuit.		3.5		ns
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		9.5		ns
Fall Time	tf	See specified Test Circuit.		15.5		ns
Total Gate Charge	Qg	V _{DS} =-6V, V _{GS} =-4.5V, I _D =-0.9A		1.43		nC
Gate-to-Source Charge	Qgs	VDS=-6V, VGS=-4.5V, ID=-0.9A		0.31		nC
Gate-to-Drain "Miller" Charge	Qgd	V _{DS} =-6V, V _{GS} =-4.5V, I _D =-0.9A		0.26		nC
Diode Forward Voltage	V _{SD}	I _S =-0.9A, V _{GS} =0		-0.98	-1.5	V

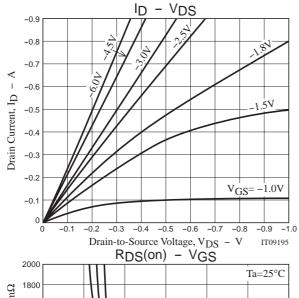
Package Dimensions

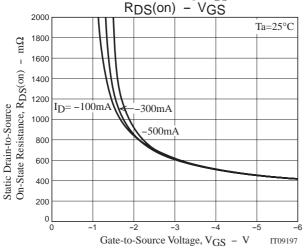
unit : mm 2245

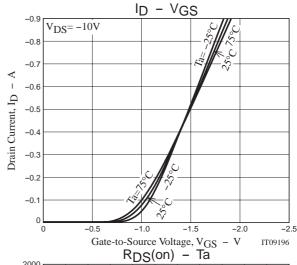


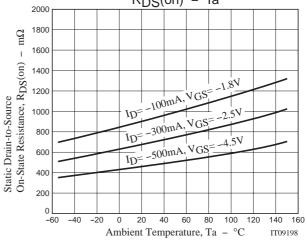
Switching Time Test Circuit

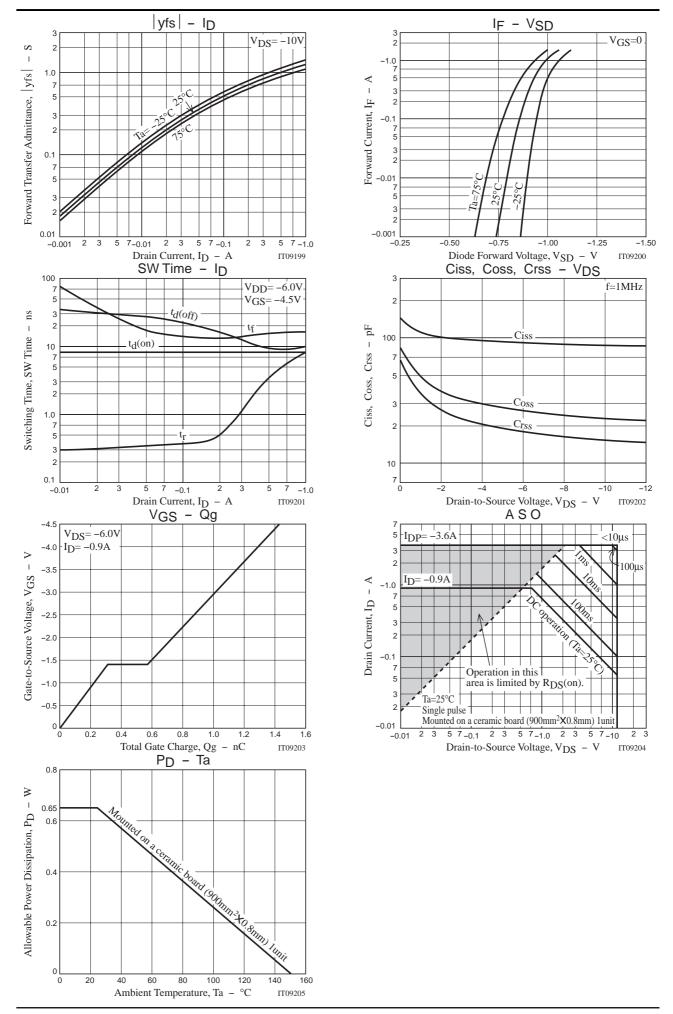












Note on usage: Since the SCH2315 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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